Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO.	SERIAL NO.
		244989US2S	New Application
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT: Tsuneo INABA	
		FILING DATE: Herewith	GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DL	AA	5,946,227	08/31/99	Peter K. NAJI			
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	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
DL	AO	2002-25245	01/25/02	Japan		x
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

DL	AV	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, DIGEST OF TECHNICAL PAPERS, February 2000, 8 Pages
DL	AW	M. DURLAM, et al., "NONVOLATILE RAM BASED ON MAGNETIC TUNNEL JUNCTION ELEMENTS", IEEE INTERNATIONAL SOILID-STATE CIRCUITS CONFERENCE, DIGEST OF TECHNICAL PAPERS, February 2000, 7 Pages
DL	AX	Peter K. NAJI, et al., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoressistive RAM", IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, DIGEST OF TECHNICAL PAPERS, February 2001, 9 Pages
DL	AY	Kouichi YAMADA, et al., "A Novel Sensing Scheme for a MRAM with a 5% MR Ratio", SYMPOSIUM ON VLSI CIRCUITS DIGEST OF TECHNICAL PAPERS, Session C12-1, June 2001, 2 Pages
	AZ	

☐ Additional References sheet(s) attached

Examiner: [signature] Date Considered 3/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.